

# Youngjin Jeon

## List of Publications by Year in descending order

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Version: 2024-02-01

21  
papers

264  
citations

1040056

9  
h-index

940533

16  
g-index

21  
all docs

21  
docs citations

21  
times ranked

290  
citing authors

#	ARTICLE	IF	CITATIONS
1	Field-effect modulation of the thermoelectric characteristics of silicon nanowires on plastic substrates. <i>Nanotechnology</i> , 2016, 27, 485401.	2.6	1
2	Low-power functionality of silicon-nanowire-assembled inverters on bendable plastics. <i>Nano Research</i> , 2016, 9, 1409-1417.	10.4	2
3	Nanowatt power operation of silicon nanowire NAND logic gates on bendable substrates. <i>Nano Research</i> , 2016, 9, 3656-3662.	10.4	4
4	NOR logic function of a bendable combination of tunneling field-effect transistors with silicon nanowire channels. <i>Nano Research</i> , 2016, 9, 499-506.	10.4	12
5	Enhancement of Trap-Assisted Green Electroluminescence Efficiency in ZnO/SiO <sub>2</sub> /Si Nanowire Light-Emitting Diodes on Bendable Substrates by Piezophototronic Effect. <i>ACS Applied Materials &amp; Interfaces</i> , 2016, 8, 2764-2773.	8.0	9
6	Electrical Characteristics of SnO <sub>2</sub> Thin-Film Transistors Fabricated on Bendable Substrates Using Reactive Magnetron Sputtering. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 11697-11700.	0.9	5
7	Flexible silicon nanowire low-power ring oscillator featuring one-volt operation. <i>Microelectronic Engineering</i> , 2015, 145, 120-123.	2.4	5
8	Steep Subthreshold Swing n- and p-Channel Operation of Bendable Feedback Field-Effect Transistors with p <sup>+</sup> -n <sup>+</sup> Nanowires by Dual-Top-Gate Voltage Modulation. <i>Nano Letters</i> , 2015, 15, 4905-4913.	9.1	47
9	Impact-Ionization and Tunneling FET Characteristics of Dual-Functional Devices With Partially Covered Intrinsic Regions. <i>IEEE Nanotechnology Magazine</i> , 2015, 14, 633-637.	2.0	15
10	Flexible semi-around gate silicon nanowire tunnel transistors with a sub-kT/q switch. <i>Journal of Applied Physics</i> , 2015, 117, 224502.	2.5	11
11	ZnO nanowire field-effect transistors with Pt nanocrystals fabricated on a flexible plastic substrate for a non-volatile memory application. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 1912-1916.	1.8	0
12	Vertical stacking of ZnO nanowire devices with different functionalities on plastic substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 1928-1932.	1.8	1
13	Switching Characteristics of Nanowire Feedback Field-Effect Transistors with Nanocrystal Charge Spacers on Plastic Substrates. <i>ACS Nano</i> , 2014, 8, 3781-3787.	14.6	28
14	Si-Nanowire-Array-Based NOT-Logic Circuits Constructed on Plastic Substrates Using Top-Down Methods. <i>Journal of Nanoscience and Nanotechnology</i> , 2013, 13, 3350-3353.	0.9	1
15	Flexible Logic Gates Composed of Si-Nanowire-Based Memristive Switches. <i>IEEE Transactions on Electron Devices</i> , 2012, 59, 3288-3291.	3.0	9
16	Flexible Nano-Floating-Gate Memory With Channels of Enhancement-Mode Si Nanowires. <i>IEEE Transactions on Electron Devices</i> , 2012, 59, 2939-2942.	3.0	10
17	Comparative performance analysis of silicon nanowire tunnel FETs and MOSFETs on plastic substrates in flexible logic circuit applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012, 209, 1350-1358.	1.8	11
18	Top-Down Fabrication of Fully CMOS-Compatible Silicon Nanowire Arrays and Their Integration into CMOS Inverters on Plastic. <i>ACS Nano</i> , 2011, 5, 2629-2636.	14.6	57

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19	Si-Based Flexible Memristive Systems Constructed Using Top-Down Methods. ACS Applied Materials & Interfaces, 2011, 3, 3957-3961.	8.0	10
20	Light-emitting diodes composed of n-ZnO and p-Si nanowires constructed on plastic substrates by dielectrophoresis. Solid State Sciences, 2011, 13, 1735-1739.	3.2	21
21	Strain-Dependent Characteristics of Triangular Silicon Nanowire-Based Field-Effect Transistors on Flexible Plastics. Japanese Journal of Applied Physics, 2011, 50, 065001.	1.5	5